77.	112	Search Text	DB	Time stamp
L Number	Hits	(("5976769") or ("5106786") or ("4820611")	USPAT;	2004/02/07 11:33
1	'	or ("5705321") or ("5625220") or	US-PGPUB;	2001, 02, 0
		("6010829") or ("5968712")).PN.	EPO; JPO;	
		(0010029) 01 (3300712) , 1111	IBM TDB	
2	8	(((resist or photoresist or energy adj	USPĀT;	2004/02/07 11:35
2		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
	,	isotropic\$4 near3 etch\$3))) and		
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or		Ì
		438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and ("SiON" or		
		silicon adj oxynitride) same (\$1ARC or		
		antireflect\$3 or anti adj reflect\$3)		0004/00/07 11.40
3	8	(((resist or photoresist or energy adj	USPAT;	2004/02/07 11:42
	2"	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and (430/5,296,313,316,317,321,329,330 or		
		378/34,35 or 438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and (hardmask or hard		
		adj mask) same (\$1ARC or antireflect\$3 or		
		anti adj reflect\$3)		
4	0	430/331.ccls. and (liquid near3	USPAT;	2004/02/07 11:43
1		isotropic\$4 same (developer or solution or	US-PGPUB;	1
		solvent or etch\$3))	EPO; JPO;	1
			IBM_TDB	
5	153	(((resist or photoresist or energy adj	USPAT;	2004/02/07 11:44
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	İ
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and	4	
		(430/5, 296, 313, 316, 317, 321, 329, 330 or		
		378/34,35 or		
		438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and (expos\$3 or pattern\$3 or radiat\$3 or irradiat\$3) same		
·		(resist or photoresist or energy adj	-	
		sensit\$4 or photosensit\$4 or photo adj	0	
		sensit\$4 or photosensit\$4 or photo day sensit\$4) same (x adj ray or extreme adj		
		ultraviolet or EUV or extreme adj UV or		
		"157" adj nm or "193" adj nm or deep adj	9)	
		ultraviolet or deep adj UV or DUV or i adj		<i>i</i>
		line or particle adj beam or ion adj beam		
		or electron adj beam or e adj beam) not		
		((((resist or photoresist or energy adj		
		sensit\$4 or photosensit\$4 or photo adj		
		sensit\$4) same (develop\$4 and (reduc\$3 or		
		shrink\$3 or decreas\$3 or less\$5 or slim\$4		
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and		
		(430/5, 296, 313, 316, 317, 321, 329, 330 or		
		378/34,35 or		
		438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or		
	-	silicon adj oxynitride) same (\$1ARC or	*	
		antireflect\$3 or anti adj reflect\$3))		
6	5		USPAT;	2004/02/07 11:44
		(developer or solution or solvent or	US-PGPUB;	
		etch\$3))	EPO; JPO;	
			IBM TDB	

				0004/00/07 11 46
7	1	((resist or photoresist or energy adj	USPAT;	2004/02/07 11:46
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	5
	!	shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	1
		or trim\$4) and (liquid or wet or solvent		
	}	or solution) and isotropic\$4 near3		
	-	etch\$3)) and liquid adj isotropic adj		
		etch\$3		
8	45	((resist or photoresist or energy adj	USPAT;	2004/02/07 11:50
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same develop\$4 same	EPO; JPO;	•
		(tetramethylammonium adj hydroxide or	IBM TDB	
		tetramethyl adj ammonium adj hydroxide or		
		TMAH)) and (weak or mild) near3 develop\$4		
	3.5		USPAT;	2004/02/07 11:51
9	35	(bak\$3 or heat\$3) same (resist or	US-PGPUB;	2004/02/07 11:31
		photoresist) same (glass adj transition		
		adj temperature or "T.sub.g") same	EPO; JPO;	
Ì		(novolac or novolak or \$6hydroxystyrene)	IBM_TDB	0000/00/14 14 16
ł –	1	("5976769").PN.	USPAT;	2003/08/14 14:16
			US-PGPUB	
-	1154	(resist or photoresist or energy adj	USPAT;	2003/08/15 14:36
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or	_	
		isotropic\$4 near3 etch\$3))		
_	610	((resist or photoresist or energy adj	USPAT;	2003/08/14 16:40
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
Ì		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and (liquid near3 etch\$3 or	-	•
-		isotropic\$4 near3 etch\$3))) and		
		(semiconduct\$3 or optic\$4 or mask or		*
		photomask or reticle).ti,ab.		·
	279	1 ~	USPAT;	2003/08/14 18:25
_	219	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	2003, 00, 21 20.20
		sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
			TBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and		
		(430/5, 296, 313, 316, 317, 321, 329, 330 or		
		378/34,35 or		
		438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.		
_	8	(((resist or photoresist or energy adj	USPAT;	2004/02/07 11:34
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and		
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or		
		438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and ("SiON" or		
		silicon adj oxynitride) same (\$1ARC or		
		antireflect\$3 or anti adj reflect\$3)		

-	151	(((resist or photoresist or energy adj	USPAT;	2003/08/15 14:13
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and (liquid near3 etch\$3 or	_	
		isotropic\$4 near3 etch\$3))) and		*
		(430/5,296,313,316,317,321,329,330 or		
	i	378/34,35 or		
	į	438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and (bak\$3 or heat\$3)		
		same (resist or photoresist or energy adj		
		sensit\$4 or photosensit\$4 or photo adj		
		sensit\$4) not ((((resist or photoresist or		
		energy adj sensit\$4 or photosensit\$4 or		
		photo adj sensit\$4) same (develop\$4 and		
		(reduc\$3 or shrink\$3 or decreas\$3 or		
		less\$5 or slim\$4 or trim\$4) and (liquid		
		near3 etch\$3 or isotropic\$4 near3		
		etch\$3))) and		
*		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or	•	
		438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and ("SiON" or		
,		silicon adj oxynitride) same (\$1ARC or		
	5	anticon adj oxymitiide) same (JiAke of anticefåeco\$3pbøtemesiadjorefhecg\$3adj	USPAT;	2004/02/07 11:41
-	5		-	2004/02/0/ 11.41
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM_TDB	
		or trim\$4) and (liquid near3 etch\$3 or		
		isotropic\$4 near3 etch\$3))) and		
		(430/5,296,313,316,317,321,329,330 or		
		378/34,35 or		
8		438/723,724,733-735,737,739,743,744,756,757		
		or 216/41,49).ccls.) and (hardmask or hard		
		adj mask) same (\$1ARC or antireflect\$3 or		
	_	anti adj reflect\$3)	HODAM.	2002/00/14 10:50
_	1	"5472829".PN.	USPAT;	2003/08/14 19:58
			US-PGPUB	0000100115
` -	1	"5139904".PN.	USPAT;	2003/08/15 11:14
			US-PGPUB	
- '	1	"5324676".PN.	USPAT;	2003/08/15 11:26
			US-PGPUB	
_	1	"5431770".PN.	USPAT;	2003/08/15 11:27
	_		US-PGPUB	
_	1	"5804088".PN.	USPAT;	2003/08/15 11:30
			US-PGPUB	
	1	"5005007" DN		2003/08/15 11:58
_	1	"5885887".PN.	USPAT;	2003/06/13 11:38
		#5000004# py	US-PGPUB	0000/00/15 10 05
-	1	"5930634".PN.	USPAT;	2003/08/15 12:01
			US-PGPUB	
-	1	"5965461".PN.	USPAT;	2003/08/15 12:02
			US-PGPUB	
_	1	"6020111".PN.	USPAT;	2003/08/15 12:14
			US-PGPUB	
_	1	"6121123".PN.	USPAT;	2003/08/15 12:54
		CECETED . FIG.	US-PGPUB	-500,00,10 12.54
_	1	"6121123".PN.	USPAT;	2003/08/15 13:03
-	1 D	0171170 · LIA.	· ·	2003/00/13 13:03
		HC1FCAOFH DV	US-PGPUB	2002/00/15 12 21
	1	"6156485".PN.	USPAT;	2003/08/15 13:04
			US-PGPUB	
-	1	"6194323".PN.	USPAT;	2003/08/15 13:12
			US-PGPUB	
_	. 1	"6277750".PN.	USPAT;	2003/08/15 13:15
			US-PGPUB	
_	1	"6281130".PN.	USPAT;	2003/08/15 13:15
		0501100 .114.	US-PGPUB	2005,00,15 15.15
		420/221 gale and /limid name?		2004/02/07 11:43
-	0	430/331.ccls. and (liquid near3	USPAT;	2004/02/0/ 11:43
		isotropic\$4 same (developer or solution or	US-PGPUB;	
		solvent or etch\$3))	EPO; JPO;	
			IBM_TDB	

			,	
138	(((resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3)) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and (expos\$3 or pattern\$3 or radiat\$3 or irradiat\$3) same (resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (x adj ray or extreme adj ultraviolet or EUV or extreme adj UV or "157" adj nm or "193" adj nm or deep adj ultraviolet or deep adj UV or DUV or i adj line or particle adj beam or ion adj beam or electron adj beam or eadj beam) not ((((resist or photosensit\$4 or photo adj sensit\$4 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3))) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same (\$1ARC or antireflect\$3 or anti adj reflect\$3)) 430/331.ccls. and (isotropic\$4 same (developer or solution or solvent or etch\$3)) (((resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4 or photosensit\$4 or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4 o	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/02/07 11	1:44
	or 216/41,49).ccls.) and (expos\$3 or pattern\$3 or radiat\$3 or irradiat\$3) same (resist or photoresist or energy adj sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (x adj ray or extreme adj ultraviolet or EUV or extreme adj UV or "157" adj nm or "193" adj nm or deep adj			
	((((resist or photoresist or energy ad) sensit\$4 or photosensit\$4 or photo adj sensit\$4) same (develop\$4 and (reduc\$3 or shrink\$3 or decreas\$3 or less\$5 or slim\$4 or trim\$4) and (liquid near3 etch\$3 or isotropic\$4 near3 etch\$3)) and (430/5,296,313,316,317,321,329,330 or 378/34,35 or 438/723,724,733-735,737,739,743,744,756,757 or 216/41,49).ccls.) and ("SiON" or silicon adj oxynitride) same (\$1ARC or antireflect\$3 or anti adj reflect\$3))			,

	1	((resist or photoresist or energy adj	USPAT;	2004/02/07 11:46
_	1 :	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	2001,02,0. 11.10
		sensit\$4 or photosensit\$4 or photo day sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and (liquid or wet or solvent	1211_122	
		or solution) and isotropic\$4 near3		
1		etch\$3)) and liquid adj isotropic adj		
1		etch\$3		
	617	(resist or photoresist or energy adj	USPAT;	2003/08/15 14:48
_	017	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	2000, 00, 20 21100
		sensit\$4) same (develop\$4 and (reduc\$3 or	EPO; JPO;	
		shrink\$3 or decreas\$3 or less\$5 or slim\$4	IBM TDB	
		or trim\$4) and (liquid or wet or solvent	12	
		or solution) and isotropic\$4 near3 etch\$3)		
	2783	(resist or photoresist or energy adj	USPAT:	2003/08/16 10:53
_	2703	sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same develop\$4 same	EPO; JPO;	
		(tetramethylammonium adj hydroxide or	IBM TDB	
		tetramethyl adj ammonium adj hydroxide or	_	
		TMAH)		
_	41	((resist or photoresist or energy adj	USPAT;	2004/02/07 11:50
		sensit\$4 or photosensit\$4 or photo adj	US-PGPUB;	
		sensit\$4) same develop\$4 same	EPO; JPO;	
		(tetramethylammonium adj hydroxide or	IBM TDB	
		tetramethyl adj ammonium adj hydroxide or	_	
		TMAH)) and (weak or mild) near3 develop\$4		
_	1	("2000112146").PN.	DERWENT	2003/08/16 13:10
_	0	("10-285215").PN.	DERWENT	2003/08/16 13:10
_	1	("10285215").PN.	DERWENT	2003/08/16 13:10
_	29	(bak\$3 or heat\$3) same (resist or	USPAT;	2004/02/07 11:50
		photoresist) same (glass adj transition	US-PGPUB;	
		adj temperature or "T.sub.g") same	EPO; JPO;	
		(novolac or novolak or \$6hydroxystyrene)	IBM TDB	